

PRODUCT/PROCESS CHANGE NOTIFICATION

PCN APM-PWR/07/2417 Notification Date 04/05/2007

Silicon Line Change for Bipolar devices-BB01 products line

PWR - PWR BIP/ IGBT/ RF

| Product Identification (Product Family/Commercial Product) | see attached list |
|---|--|
| Type of change | Waferfab process change |
| Reason for change | To improve performances |
| Description of the change | Planar Base Island technology ready to replace the mature Epibase technology in order to align our products to the actual Market. The line BB01 will replace the old ones B004 Feature: Improved hFE linearity and Higher fT frequency benefit: Better performances in switching and linear application. |
| Product Line(s) and/or Part Number(s) | See attached |
| Description of the Qualification Plan | See attached |
| Change Product Identification | See "N" in additional info on P/N. |
| Manufacturing Location(s) | |

Table 1. Change Identification

Table 2. Change Implementation Schedule

| Forecasted implementation date for change | 30-Jun-2007 |
|---|-------------|
| Forecasted availabillity date of samples for customer | 29-Mar-2007 |
| Forecasted date for STMicroelectronics change Qualification Plan results availability | 29-Mar-2007 |
| Estimated date of changed product first shipment | 05-Jul-2007 |

Table 3. List of Attachments

| Customer Part numbers list | |
|----------------------------|--|
| Qualification Plan results | |

| | × |
|---|------------------------------|
| Customer Acknowledgement of Receipt | PCN APM-PWR/07/2417 |
| Please sign and return to STMicroelectronics Sales Office | Notification Date 04/05/2007 |
| Qualification Plan Denied | Name: |
| Qualification Plan Approved | Title: |
| | Company: |
| 🗖 Change Denied | Date: |
| Change Approved | Signature: |
| Remark | |
| | |
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| Name | Function |
|---------------------------|----------------------------|
| Lanzafame, Alfio Salvator | Division Marketing Manager |
| Porto, Michele Claudio | Division Product Manager |
| Falcone, Giuseppe | Division Q.A. Manager |

| | APM CATANIA RELIABILITY REPORT | Date: | Mar '07 |
|--|-----------------------------------|-------|---------|
| | | No | 01/07 |

Reliability evaluation

on

BB01 for silicon line change on TIP122

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Introduction

This report is aimed to qualify the new line BB01 for line change on device TIP122

The Qualification Reliability test trials have been performed in ST Catania Site.

The evaluation results meet ST products qualification targets, therefore the new line BB01 for silicon line change on TIP122 is qualified.

| | APM CATANIA RELIABILITY REPORT | Date: | Mar '07 |
|--|-----------------------------------|-------|---------|
| | | No | 01/07 |

Test Vehicles :

| Product Line | Sales Type | Package |
|--------------|------------|---------|
| BB01 | TIP122 | TO-220 |

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Failure Criteria :

A failed component is a device which becomes inoperative during the test or it fails on meeting the end limits foreseen in the device specification, for one or more than the parameters here below reported

Parameter Power BIPOLAR Main Parameter

Collector Leakage Current (Icbo or Iceo or Ices, etc...) Emitter Leakage (Iebo) HFE, Vcesat, Vbesat, Vf Breakdown Voltage (BVcbo, BVceo,Vbces, Bvebo)

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Reliability Evaluation Plan and results

D.U.T.: TIP122 LINE: BB01 PACKAGE: TO-220

| Test | Conditions | S.S. | Requirement | Results |
|------------------------------|-----------------------------------|---------------|--|---|
| H.T.S. | TA=150°C | 77 x 1 Lot | Parameter deviation within spec. limits at 1000 hours. | No parameter deviation out of spec. limits at 1000 hours. |
| T.H.B. | TA=85℃ - RH=85% Vbias= 100V | 77 x 1 Lot | Parameter deviation within spec. limits at 1000 hours. | No parameter deviation out of spec. limits at 1000 hours. |
| H.T.R.B. | T.A.=150℃ Vdd=80V | 77 x 1 Lot | Parameter deviation within spec. limits at 1000 hours. | No parameter deviation out of spec. limits at 1000 hours. |
| PRESSURE POT | TA=121°C - PA=2Atm | 77 x 1 Lot | Parameter deviation within spec. limits at 96 hours. | No parameter deviation out of spec. limits at 96 hours. |
| THERMAL CYCLES AIR TO AIR | TA=-65℃ TO 150℃ 1 HOUR / CYCLE | 77 x 1 Lot | Parameter deviation within spec. limits at 500 cycles. | No parameter deviation out of spec. limits at 500 cy |
| THERMAL FATIGUE | ∆TC=105℃ - Pd=4.8W | 77 x 1 Lot | Parameter deviation within spec. limits at 10k cycles. | No parameter deviation out of spec. limits at 10Kcy. |

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Technological Characteristics

D.U.T.: TIP122

LINE: BB01

PACKAGE: TO-220

| DIE | Technology: Material: Metallization – Front : - Back : | Planar Silicon Al/Si Au-As/Cr/Ni/Au | Passivation : Dimensions : | • |
|---------------|---|--|--|--|
| DIE ATTACH | Soft Solder | FRAME | Frame and lead material: Frame coating : Lead coating : | Cu Ni/NiP Plated Sn 100% |
| WIRE BOND | Ultrasonic | WIRE | Material : Diameter : | Al/Mg Base Al/Mg Emitter 5 mils Base 7 mils Emitter |
| SEALING | Molding | PACKAGING | Material : | Epoxy Resin |

PRODUCTION PLACES: WAFER PROCESSING : SINGAPORE ASSEMBLY LOCATION : CASABLANCA/SHENZHEN/PSI LAGUNA QA LOCATION : CASABLANCA/SHENZHEN/PSI LAGUNA

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Reliability Test Description

High Temperature Reverse Bias (HTRB)

This test is performed in order to demonstrate the quality and reliability of devices subjected to an elevated temperature and simultaneously reverse biased. The purpose of this test is to detect surface defects such as poor passivation, presence of contaminants, etc...

High Temperature Storage (HTS)

This stress test is performed to check the device life in a high temperature ambient. Specimens are put for a period of time inside a stove in free air. Detectable failure mechanisms are presence of contaminants and metal corrosion.

Temperature Humidity Bias (THB)

This test is performed to check the device life in a high humidity ambient. Specimens are subjected to a permanent bias in a climatic chamber in the presence of steam. Detectable failure mechanisms are metal corrosion and molding defects.

Pressure Pot

This test is performed in order to check device life in a high humidity ambient in an accelerated way. Specimens are subjected for a period of time inside an autoclave in the presence of steam and pressure. Detectable failure mechanism is metal corrosion.

Thermal Fatigue

This test is performed to demonstrate the quality and reliability of devices exposed to cyclic variation in electrical stress between "on" and "off" conditions and resultant cyclic variation in device and case temperatures (thermo-mechanical stress). The purpose of this test is to detect assembly defects: improper die-attach, bonding weakness and thermal mismatch among various components of the package.

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